Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3008070	memory or storage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/19 11:06
L2	244556	1 and (nonvolatile or non-volatile or floating adj gate or flash)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/19 11:07
L3	144	2 and cell with (two or "2") near3 bit with end	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	. 2005/01/19 11:16
L4	7	3 and compar\$5 with first adj3 bit	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/19 11:11
L5	4	4 and (writ\$5 or program\$6) with second near3 bit	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/19 11:12
L6	34	3 and (voltage or potential or level) with (program\$6 or writ\$5) near3 verif\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/19 11:18
L7	19	6 and (voltage or potential or level) with read\$5 with drain	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/19 11:18
L8	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	7 and (voltage or potential or level) with (program\$6 or writ\$5) near3 verif\$6 with drain	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/19 11:18